GaAs Semiconductor Laser Diode Single Emitter Structure



**BA** Laser

PRELIMINARY SPECIFICATION

# EYP-BAL-1064-08000-4020-CMT04-0000

General Product Information				
Product	Application			
1064 nm Broad Area Laser	Material Processing			
mounted on C-Mount	Medical			

### Absolute Maximum Ratings

	Symbol	Unit	min	typ	max
Storage Temperature	Ts	°C	-40		85
Operational Temperature at Case	T <sub>c</sub>	°C	5		40
Forward Current	l <sub>F</sub>	А			15
Reverse Voltage	V <sub>R</sub>	V			0
Output Power	P <sub>opt</sub>	W			9

#### **Recommended Operational Conditions**

	Symbol	Unit	min	typ	max
Operational Temperature at Case	T <sub>C</sub>	°C	15		30
Forward Current	I <sub>F</sub>	А			13
Output Power	P <sub>opt</sub>	W			8

### Characteristics at T<sub>amb</sub> 25 °C at Begin Of Life

λ <sub>c</sub> nm Δλ nm	1049	9 1064	1079 6
			6
/ IT //			
/dT nm/k	K	0.4	
o <sub>pt</sub> W	8		
η <sub>d</sub> W/A	0.6	0.7	
I <sub>th</sub> A			2.5
	opt W Nd W/A	opt W 8 Id W / A 0.6	opt W 8 Id W/A 0.6 0.7



#### Measurement Conditions / Comments

non condensing

non condensing

Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device. Operation at the Absolute Maximum Rating for extended periods of time can adversely affect the device realibility and may lead to reduced operational life.

Measurement Conditions / Comments
measured at position A (see drawing on p. 3)

#### Measurement Conditions / Comments

see images on page 4

total output measured with integrating sphere

eagleyard Photonics GmbH

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### Characteristics at T<sub>amb</sub> 25 °C at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Operational Current @ $P_{opt} = 8 W$	I <sub>op</sub>	А			13
Stripe Width	Ws	μm		200	
Cavity Length	L	μm		4000	
Divergence parallel (FWHM)	$\Theta_{  }$	0		10	
Divergence perpendicular (FWHM)	$\Theta_{\perp}$	0		30	
Spectral Mode (longitudinal)				Multi Mode	
Polarization				TE	

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Polarization	in nornon	dicular n	lano	

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PRELIMINARY SPECIFICATION



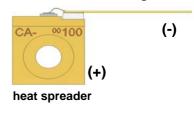
# EYP-BAL-1064-08000-4020-CMT04-0000

S				
Symbol	Unit	min	typ	max
l	mm	7.05	7.20	7.35
d	mm		4	
		Symbol Unit	Symbol Unit min I mm 7.05	Symbol Unit min typ I mm 7.05 7.20

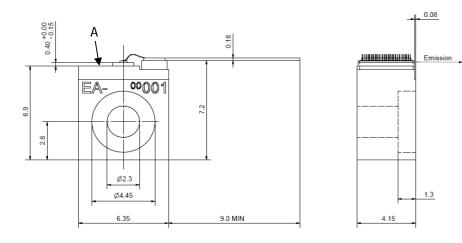
### Package Pinout

Cathode (-)	Mounting Wire
Anode (+)	Housing

mounting wire



### Package Drawings





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#### **Typical Measurement Results**

Spectrum at Specified Optical Output Power: t.b.d.

Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

#### Ordering Information:

optix

800 Village Walk #316 Guilford, CT 06437 Ph: 203-401-8093

Email orders to: <u>sales@xsoptix.com</u> Fax orders to: 800-878-7282

#### Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The BAL diode type is known to be sensitive against thermal stress. Operating at moderate temperatures on propper heat sinks will contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase thread to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.





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